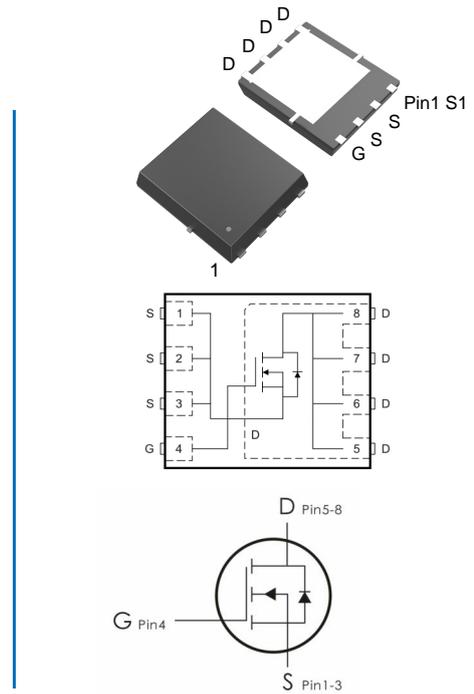


## Description:

This N-Channel MOSFET uses advanced SGT technology and design to provide excellent  $R_{DS(on)}$  with low gate charge. It can be used in a wide variety of applications.

## Features:

- 1)  $V_{DS}=40V, I_D=100A, R_{DS(ON)}<3m\ \Omega @V_{GS}=10V$  (Typ:  $2.5m\ \Omega$ )
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density SGT technology for ultra low  $R_{DS(ON)}$ .
- 5) Excellent package for good heat dissipation.
- 6) MSL3



## Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
ND2R8TG	D2R8T	DFN5*6-8	5000 pcs/Reel

## Absolute Maximum Ratings: ( $T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain-Source Voltage	40	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current <sup>1</sup>	100	A
	Continuous Drain Current- $T_C=100^\circ\text{C}$ <sup>1</sup>	70	
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	400	
$P_D$	Power Dissipation	85	W
$E_{AS}$	Single pulse avalanche energy <sup>3</sup>	125	mJ
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55-+150	$^\circ\text{C}$

## Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.47	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	50	$^\circ\text{C}/\text{W}$

**Electrical Characteristics:** ( $T_C=25^{\circ}\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\ \mu\text{A}$	40	---	---	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=40V$	---	---	1	$\mu\text{A}$
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0A$	---	---	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\ \mu\text{A}$	1.2	1.5	2.5	V
$R_{DS(on)}$	Drain-Source On Resistance <sup>3</sup>	$V_{GS}=10V, I_D=20A$	---	2.5	3.0	$\text{m}\Omega$
		$V_{GS}=4.5V, I_D=10A$	---	3.3	4	$\text{m}\Omega$
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=20V, V_{GS}=0V, f=1\text{MHz}$	---	1980	---	pF
$C_{oss}$	Output Capacitance		---	1073	--	
$C_{rss}$	Reverse Transfer Capacitance		---	46	---	
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On Delay Time	$V_{DS}=20V, I_D=50A,$ $R_{ENG}=1.6\ \Omega, V_{GS}=10V$	---	14	---	ns
$t_r$	Rise Time		---	5	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	47	---	ns
$t_f$	Fall Time		---	11	---	ns
$Q_g$	Total Gate Charge	$V_{GS}=10V, V_{DS}=20V,$ $I_D=50A$	---	36	---	nC
$Q_{gs}$	Gate-Source Charge		---	6.2	---	nC
$Q_{gd}$	Gate-Drain "Miller" Charge		---	5.6	---	nC
<b>Drain-Source Diode Characteristics</b>						
$V_{SD}$	Diode Forward Voltage	$V_{GS}=0V, I_{SD}=15A$	---	---	1.2	V
$I_S$	Continuous Drain Current	$V_D=V_G=0V$	---	---	83.3	A
$I_{SM}$	Pulsed Drain Current		---	---	333.	A
$T_{rr}$	Reverse Recovery Time	$I_F=50A,$	---	68	---	ns
$Q_{rr}$	Reverse Recovery Charge	$di/dt=100A/\mu\text{s}$	---	14	---	nC

## Notes:

1. Computed continuous current assumes the condition of  $T_{j,Max}$  while the actual continuous current depends on the thermal & electro-mechanical application board design
2. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
3. EAS condition :  $T_J=25^{\circ}C, V_{DD}=20V, V_G=10V, L=0.5mH$
4. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 0.5\%$

## Typical Characteristics: ( $T_C=25^{\circ}C$ unless otherwise noted)

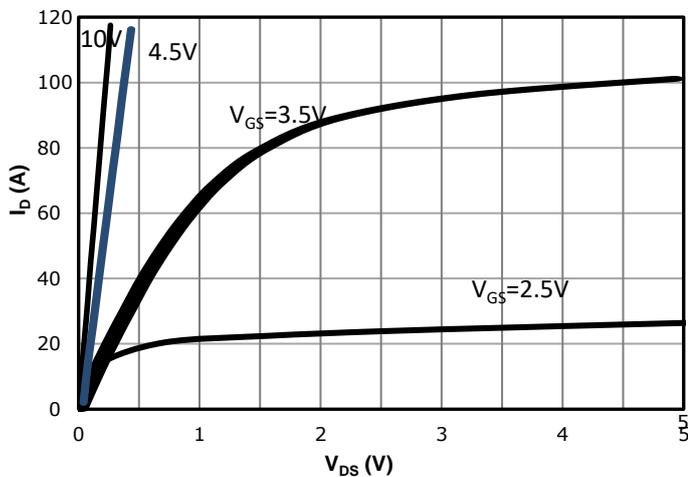


Fig 1: Output Characteristics

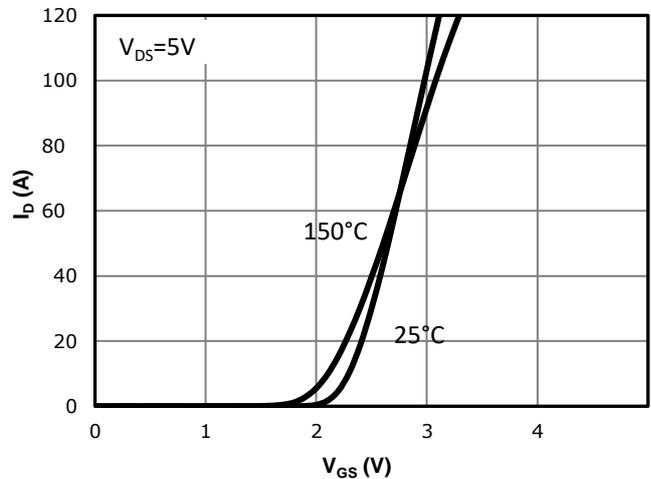


Fig 2: Transfer Characteristics

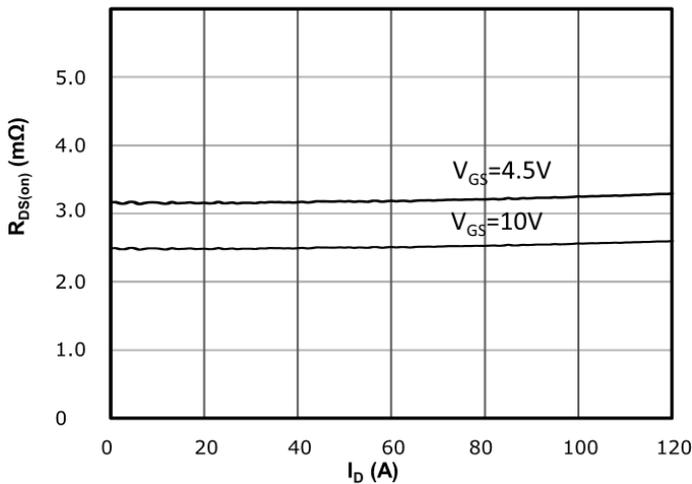


Fig 3:  $R_{DS(on)}$  vs Drain Current and Gate Voltage

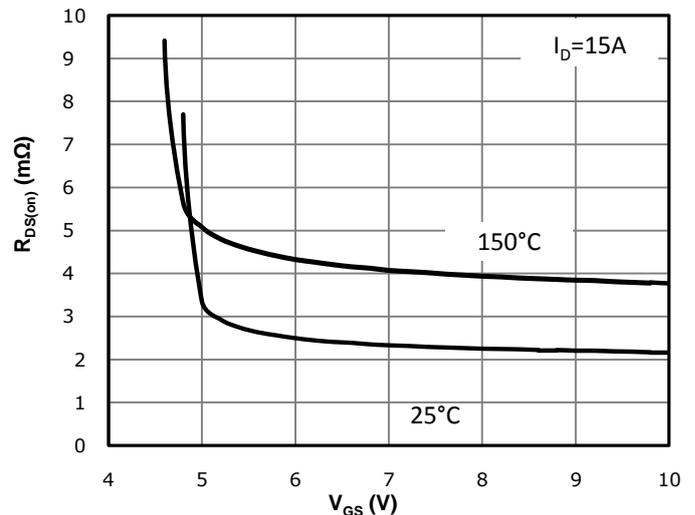


Fig 4:  $R_{DS(on)}$  vs Gate Voltage

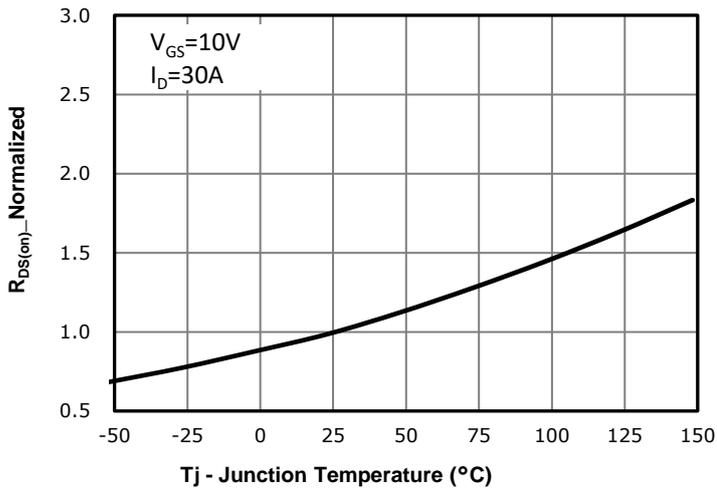


Fig 5: Rds(on) vs. Temperature

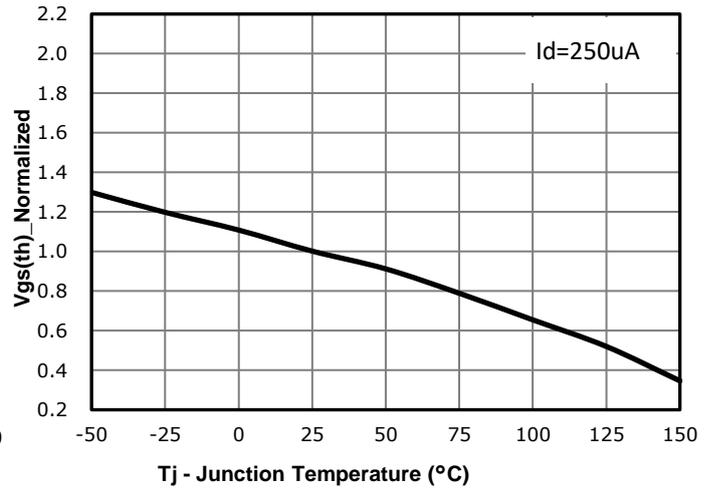


Fig 6: Vgs(th) vs. Temperature

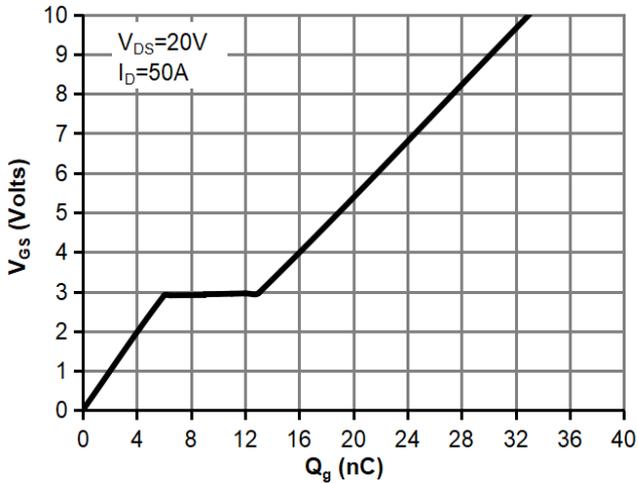


Fig 7: Gate Charge Characteristics

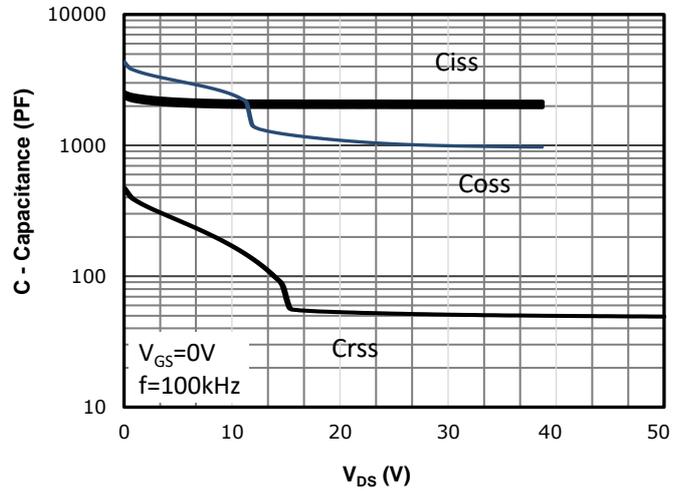


Fig 8: Capacitance Characteristics

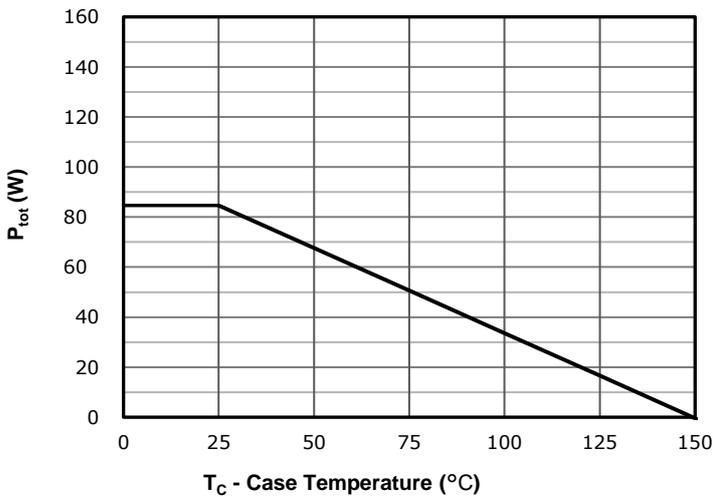


Fig 9: Power Dissipation

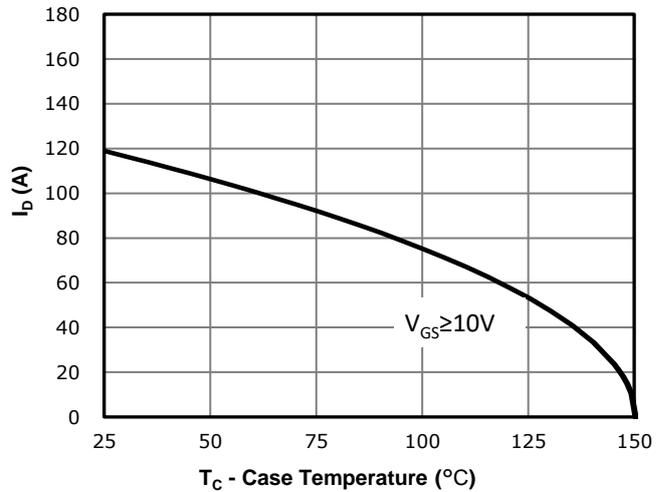
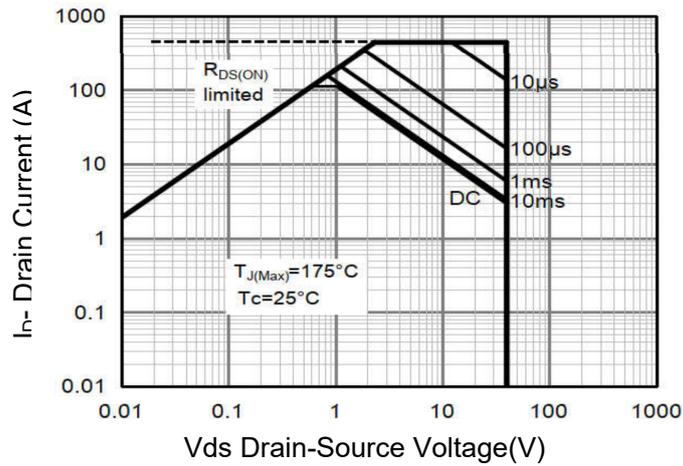
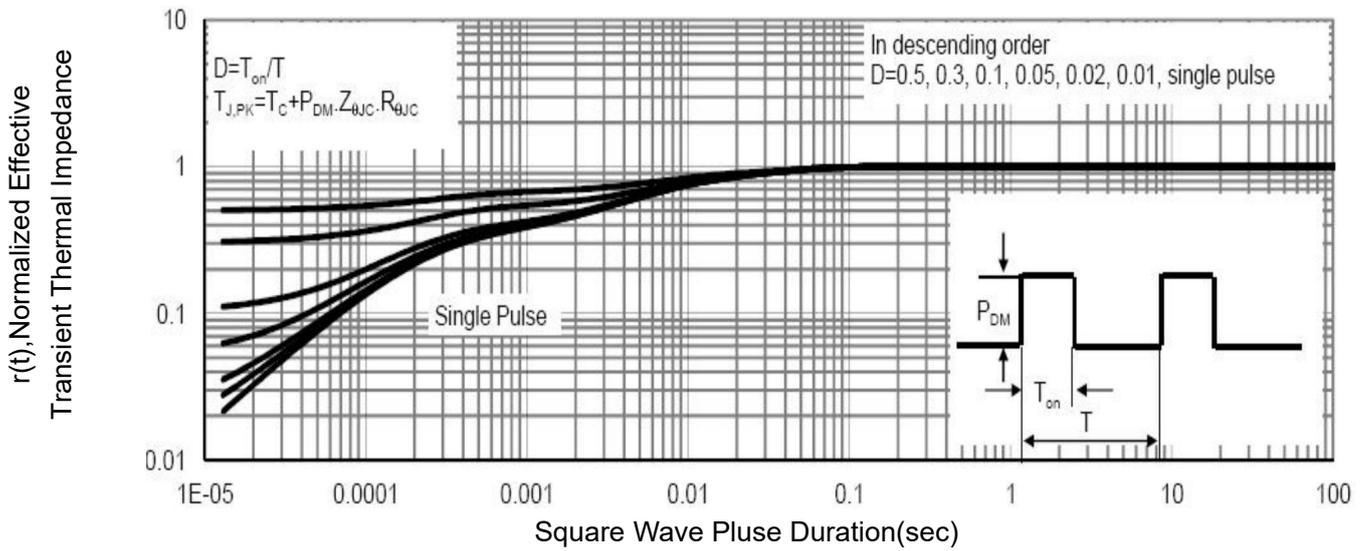


Fig 10: Drain Current Derating

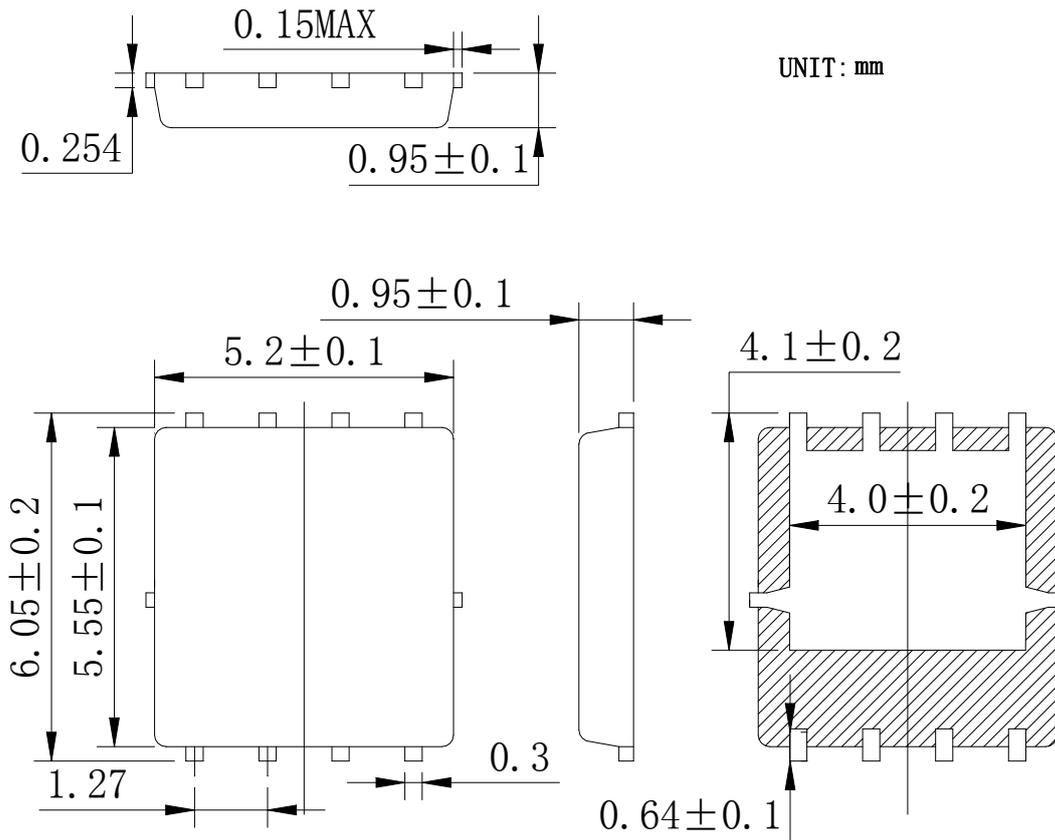


**Figure 11 Safe Operation Area**



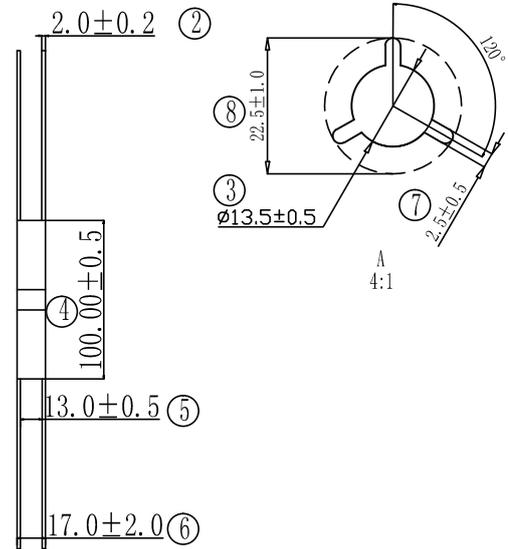
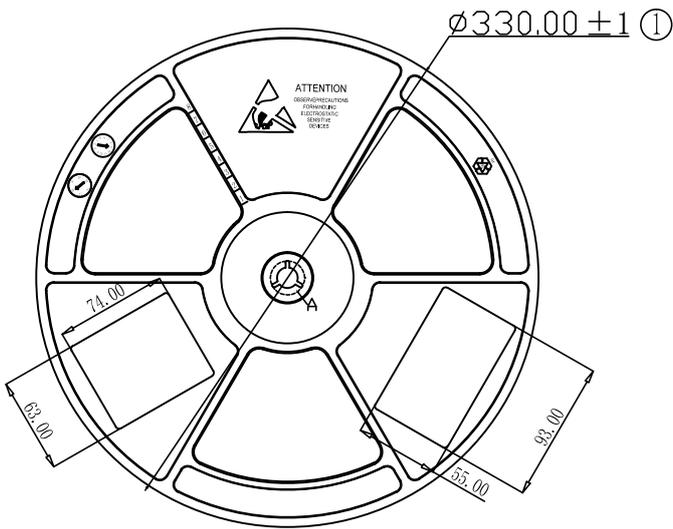
**Figure 12 Normalized Maximum Transient Thermal Impedance**

## DFN5x6-8 Package Information:

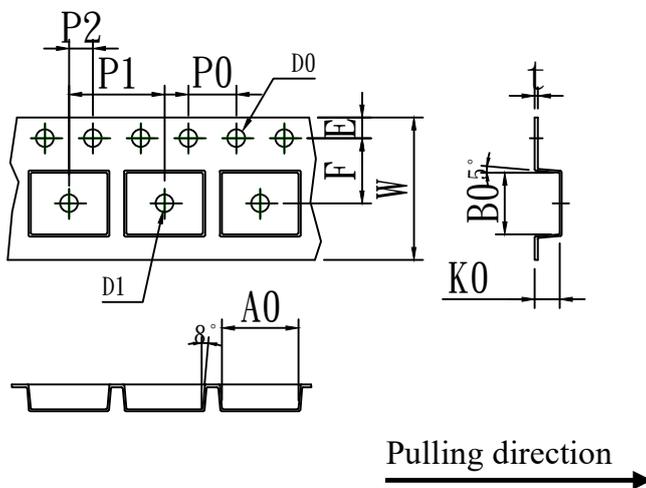


## Tape & Reel Information

Dimensions in mm



Symbol	A0	B0	K0	D0	D1	P0	P1	10*P0
Spec	$6.15 \pm 0.10$	$5.40 \pm 0.10$	$1.30 \pm 0.10$	$1.55 \pm 0.10$	$1.55 \pm 0.10$	$4.00 \pm 0.10$	$8.00 \pm 0.10$	$40.00 \pm 0.10$
Symbol	W	E	F	P2	t			
Spec	$12.00 \pm 0.10$	$1.75 \pm 0.10$	$5.50 \pm 0.10$	$2.00 \pm 0.10$	$0.20 \pm 0.05$			



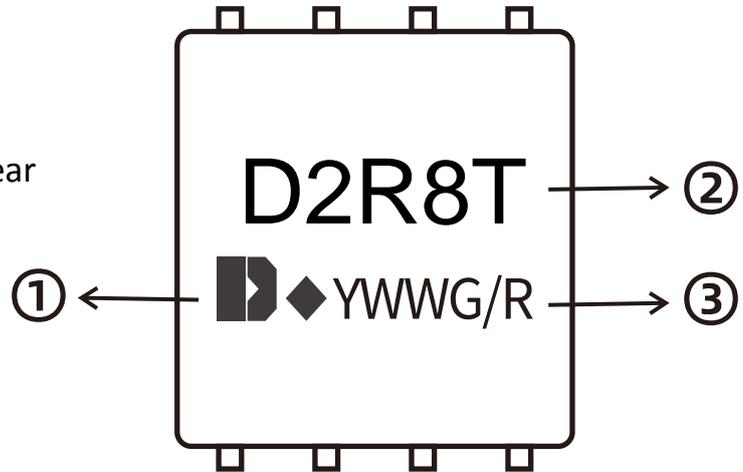
## Marking Information:

- ①. Doingter LOGO
- ②. Part NO.
- ③. Date Code(YWWG / R)

Y : Year Code , last digit of the year

WW : Week Code(01-53)

G/R : G(Green) /R(Lead Free)



## Previous Version

Version	Date	Subjects (major changes since last revision)
1.2	2025-08-30	Release of final version

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